

- 14 -

Abstract

There is provided a method of manufacturing a thin film, in which not only high crystallinity and surface flatness can be realized but also dopant doping can be
5 performed at high concentration. The method includes a low temperature highly doped layer growing step of performing dopant doping while growing the thin film at a given first temperature; an annealing step of interrupting the growth of the thin film and annealing the thin film at a given second temperature higher than the first temperature; and a high temperature lowly doped layer growing step
10 of growing the thin film at the second temperature.